High-performance polymer field-effect transistors fabricated with low-bandgap DPP-based semiconducting materials

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S1. Thermogravimetric analysis (TGA) of PDMOTT-n.
S2. Electrochemical properties of PDMOTT-n.
S3. AFM topography images of PDMOTT-n pristine thin films.
S4. 1D-GIXRD patterns of the PDMOTT-n thin films
S5. 1H and 13C NMR spectra of intermediates 2 and 3.
S1. Thermogravimetric analysis (TGA) of PDMOTT-\textit{n}.

![TGA traces of copolymers PDMOTT-\textit{n}](image)

Fig. S1 TGA traces of copolymers PDMOTT-\textit{n}.

S2. Electrochemical properties of PDMOTT-\textit{n}.

![CV traces of copolymers PDMOTT-\textit{n}](image)

Fig. S2 CV traces of copolymers PDMOTT-\textit{n}.
AFM topography images of PDMOTT-\textit{n} pristine thin films.

Fig. S3 AFM topography images of PDMOTT-\textit{n} pristine thin films on OTS-modified SiO\textsubscript{2}/Si substrates. (a) PDMOTT-118, (b) PDMOTT-122, (c) PDMOTT-320 and (d) PDMOTT-420. All images are 5 \textmu m \times 5\textmu m in size.
S4. 1D-GIXRD patterns of the PDMOTT-\( n \) thin films

Fig. S4 GIXRD patterns of the PDMOTT-\( n \) thin films after annealing at 180 °C. (a) Out-of-plane X-ray diffraction pattern. (b) In-plane X-ray diffraction pattern.
S5. $^1$H and $^{13}$C NMR spectra of intermediates 2 and 3.